

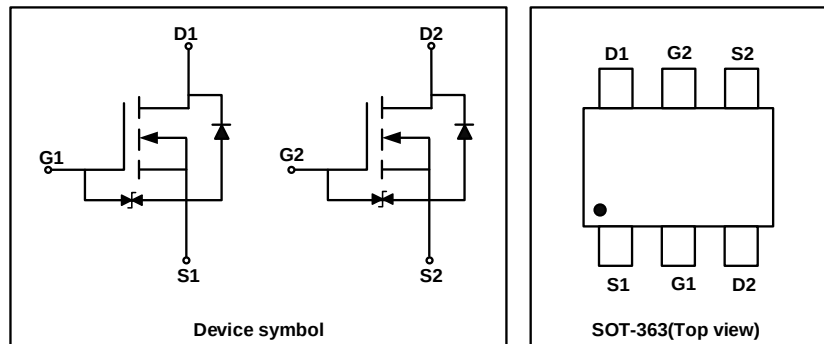
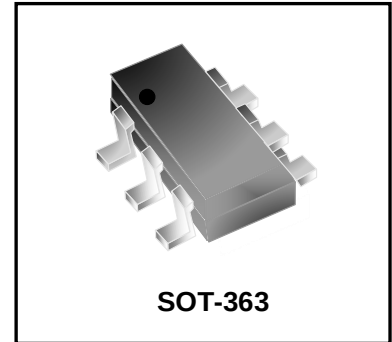
Features

- Way-on Small Single MOSFETs
- $V_{DS} = 20V$, $I_D = 0.75A$
 $R_{DS(on)} < 0.38\Omega$ @ $V_{GS} = 4.5V$
 $R_{DS(on)} < 0.45\Omega$ @ $V_{GS} = 2.5V$
- Trench LV MOSFET Technology
- ESD Protected

Mechanical Characteristics

- SOT-363 Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Absolute Maximum Rating ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	0.75	A
Pulsed Drain Current ¹	I_{DM}	3	A
Power Dissipation	P_D	250	mW
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	500	$^\circ C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	20	-	-	V
Gate-body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 8\text{V}$	-	-	± 20	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA
Gate threshold voltage ³	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.35	0.75	1.1	V
Drain-Source On-state Resistance ³	$R_{DS(on)}$	$V_{GS} = 4.5\text{V}, I_D = 0.65\text{A}$	-	0.19	0.38	Ω
		$V_{GS} = 2.5\text{V}, I_D = 0.55\text{A}$	-	0.29	0.45	
		$V_{GS} = 1.8\text{V}, I_D = 0.45\text{A}$	-	0.70	-	
Dynamic Characteristics ⁴						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 10\text{V},$ $f = 1\text{MHz}$	-	26.5	-	pF
Output Capacitance	C_{oss}		-	11	-	
Reverse Transfer Capacitance	C_{rss}		-	5.2	-	
Switching Characteristics ⁴						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V},$ $I_D = 0.5\text{A}, R_{GEN} = 10\Omega$	-	6.7	-	ns
Rise Time	t_r		-	4.8	-	
Turn-off Delay Time	$t_{d(off)}$		-	17.3	-	
Fall Time	t_f		-	7.4	-	
Source-Drain Diode Characteristics						
Body Diode Voltage	V_{SD}	$I_S = 0.15\text{A}, V_{GS} = 0\text{V}$	-	-	1.2	V
Continuous Source Current	I_S		-	-	0.75	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$
2. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

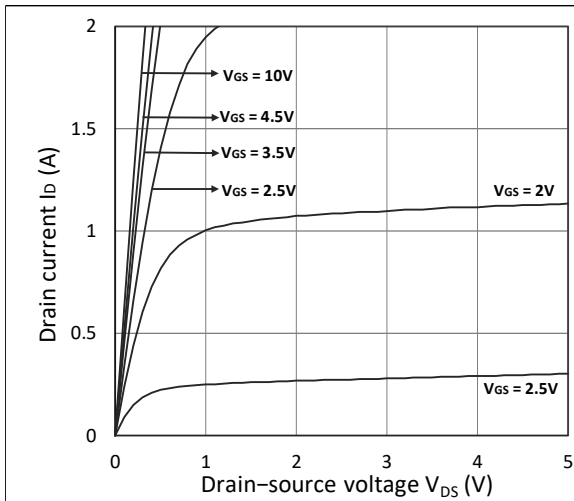


Figure 1. Output Characteristics

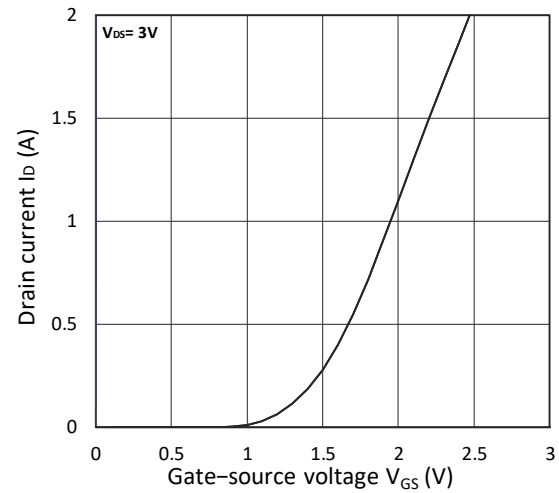


Figure 2. Transfer Characteristics

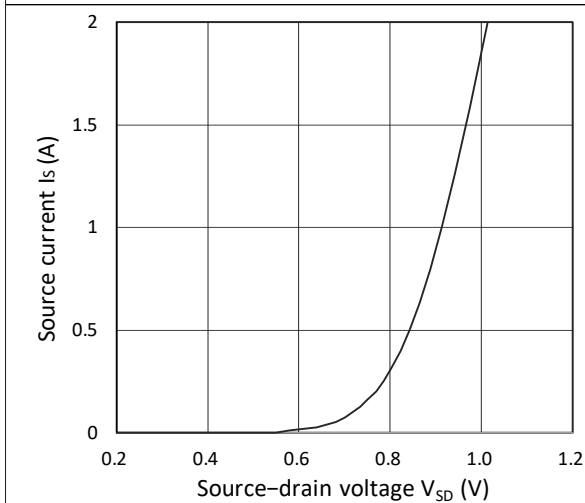


Figure 3. Forward Characteristics of Reverse

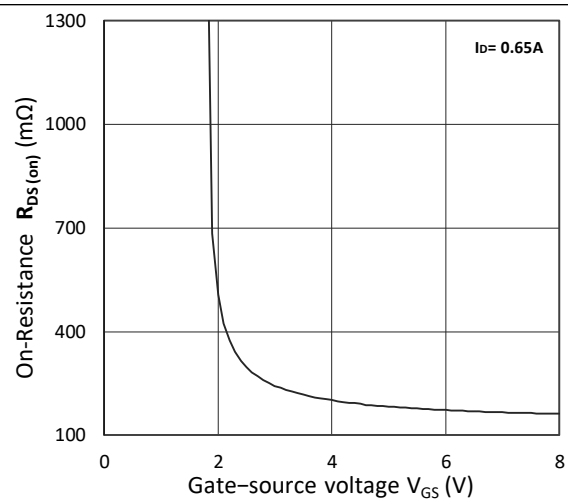
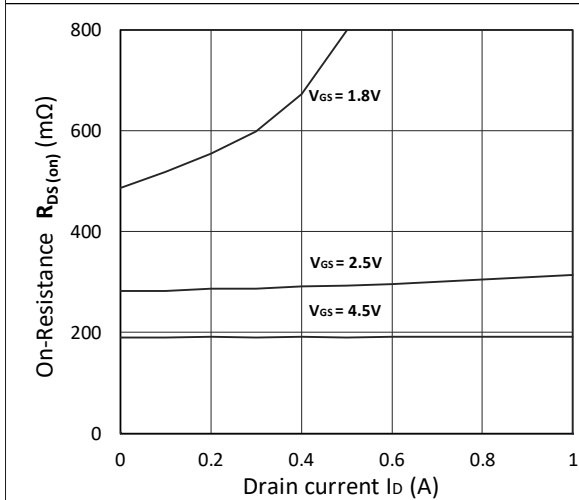
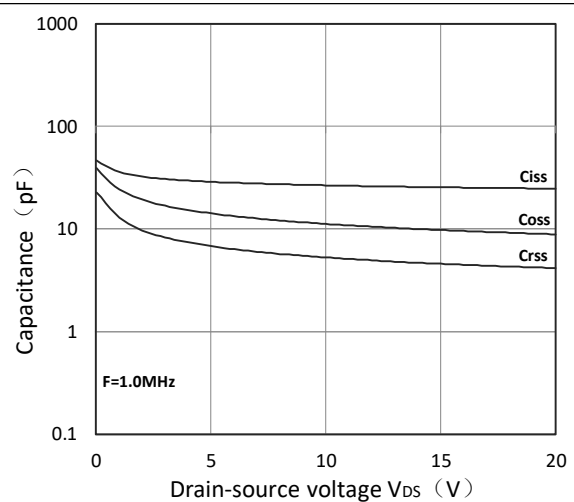
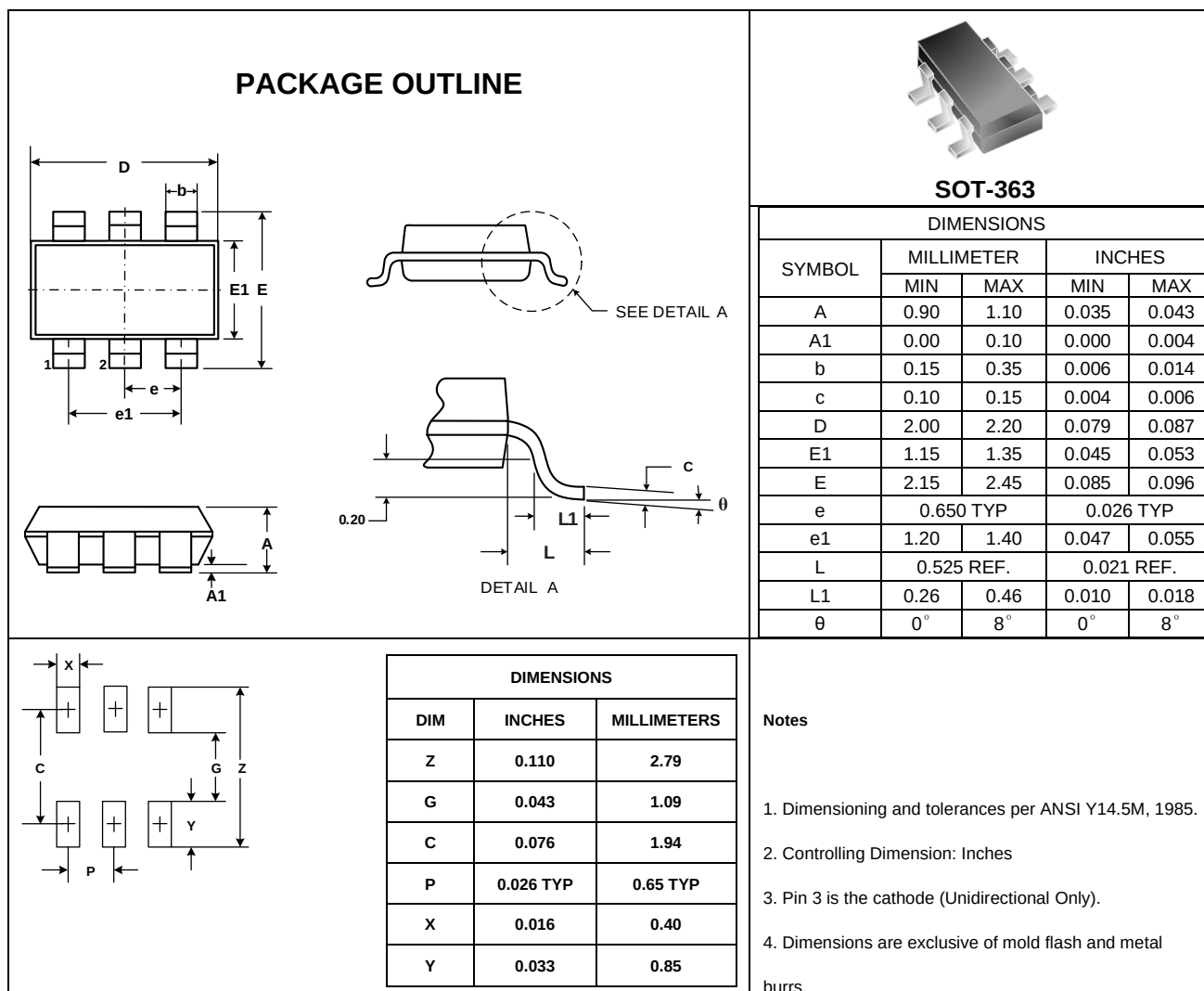
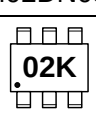
Figure 4. $R_{DS(ON)}$ vs. V_{GS} Figure 5. $R_{DS(ON)}$ vs. I_D 

Figure 6. Capacitance Characteristics

Outline Drawing – SOT-363



Marking Codes

Part Number	WM02DN08DR
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time. Users should verify actual device performance in their specific applications.